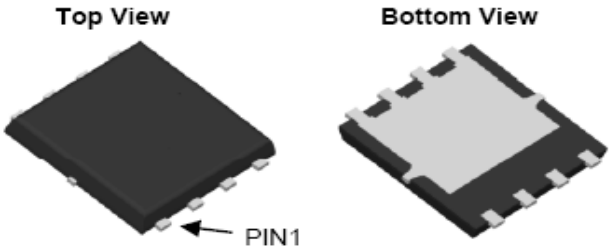
FNK75N45

N-Channel Trench Power MOSFET

General Description

The FNK75N45 is N-channel MOS Field Effect Transistor designed for high current switching applications. Rugged E_{AS} capability and ultra low $R_{DS(ON)}$ is suitable for PWM, load switching especially for E-Bike controller applications.

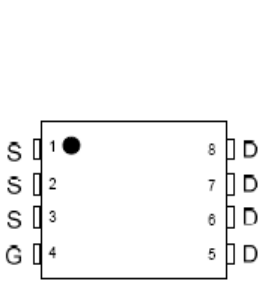


Features

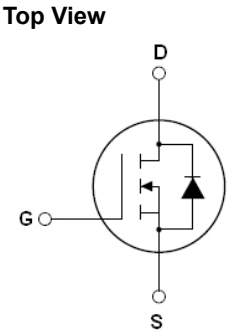
- V_{DS}=75V; I_D=65A@ V_{GS}=10V;
  $R_{DS(ON)}$<8.25mΩ @ V_{GS}=10V
- Special Designed for E-Bike Controller Application
- Ultra Low On-Resistance
- High UIS and UIS 100% Test

Application

- 64V E-Bike Controller Applications
- Hard Switched and High Frequency Circuits
- Uninterruptible Power Supply



Top View



Schematic Diagram

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
FNK75N45	FNK75N45	DFN5*6-8	-	-	-

Table 1. Absolute Maximum Ratings (TA=25℃)

Symbol	Parameter	Value	Unit
V_{DS}	Drain-Source Voltage (V_{GS}=0V)	75	V
V_{GS}	Gate-Source Voltage (V_{DS}=0V)	±25	V
$I_{D\ (DC)}$	Drain Current (DC) at Tc=25℃	65	A
$I_{D\ (DC)}$	Drain Current (DC) at Tc=100℃	45	A
$I_{DM\ (pluse)}$	Drain Current-Continuous@ Current-Pulsed **(Note 1)**	260	A
dv/dt	Peak Diode Recovery Voltage	30	V/ns
P_D	Maximum Power Dissipation(Tc=25℃)	78	W
	Derating Factor	0.93	W/℃
E_{AS}	Single Pulse Avalanche Energy **(Note 2)**	120	mJ
T_J,T_{STG}	Operating Junction and Storage Temperature Range	-55 To 175	℃

Notes 1.Repetitive Rating: Pulse width limited by maximum junction temperature

2.E_{AS} condition:T_J=25℃,V_{DD}=35V,V_G=10V,R_G=25Ω

Table 2. Thermal Characteristic

Symbol	Parameter	Value	Unit
$R_{\theta JC}$	Thermal Resistance,Junction-to-Case	3.08	℃/W

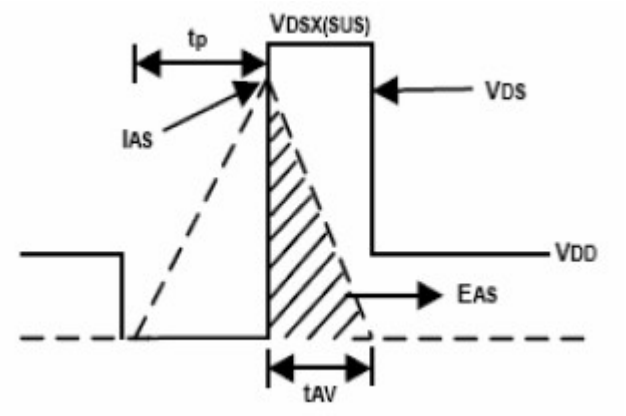
Table 3. Electrical Characteristics (TA=25℃unless otherwise noted)

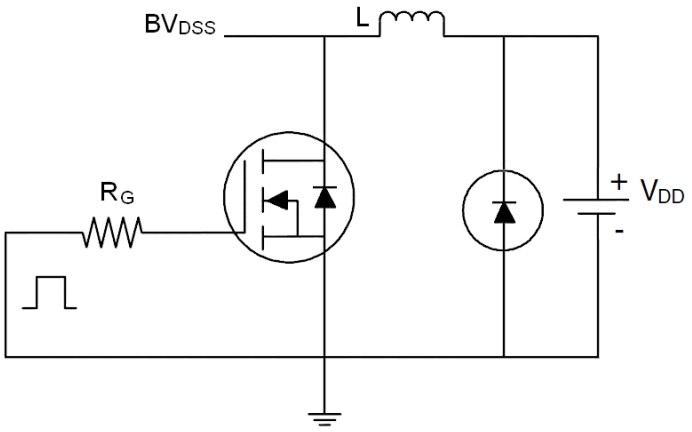
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
On/Off States						
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V I_D=250μA	75			V
I_{DSS}	Zero Gate Voltage Drain Current(Tc=25℃)	V_{DS}=82V,V_{GS}=0V			1	μA
I_{DSS}	Zero Gate Voltage Drain Current(Tc=125℃)	V_{DS}=82V,V_{GS}=0V			10	μA
I_{GSS}	Gate-Body Leakage Current	V_{GS}=±20V,V_{DS}=0V			±100	nA
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS},I_D=250μA	2		4	V
$R_{DS(ON)}$	Drain-Source On-State Resistance	V_{GS}=10V, I_D=40A		7.0	8.25	mΩ
Dynamic Characteristics						
g_{FS}	Forward Transconductance	V_{DS}=25V,I_D=40A	110			S
C_{iss}	Input Capacitance	V_{DS}=25V,V_{GS}=0V, f=1.0MHz		5884		PF
C_{oss}	Output Capacitance			860		PF
C_{rss}	Reverse Transfer Capacitance			476		PF
Q_g	Total Gate Charge	V_{DS}=50V,I_D=40A, V_{GS}=10V		106		nC
Q_{gs}	Gate-Source Charge			19		nC
Q_{gd}	Gate-Drain Charge			47.9		nC
Switching Times						
$t_{d(on)}$	Turn-on Delay Time	V_{DD}=30V,I_D=2A,R_L=15Ω V_{GS}=10V,R_G=2.5Ω		15		nS
t_r	Turn-on Rise Time			18		nS
$t_{d(off)}$	Turn-Off Delay Time			31		nS
t_f	Turn-Off Fall Time			38		nS
Source-Drain Diode Characteristics						
I_{SD}	Source-drain Current(Body Diode)			92		A
I_{SDM}	Pulsed Source-Drain Current(Body Diode)			368		A
V_{SD}	Forward On Voltage**(Note 1)**	T_J=25℃,I_{SD}=40A,V_{GS}=0V		0.8	0.95	V
t_{rr}	Reverse Recovery Time**(Note 1)**	T_J=25℃,I_F=75A di/dt=100A/μs		56		nS
Q_{rr}	Reverse Recovery Charge**(Note 1)**			113		nC
t_{on}	Forward Turn-on Time	Intrinsic turn-on time is negligible(turn-on is dominated by L_S+L_D)				

Notes 1.Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 1.5%, R_G=25Ω, Starting T_J=25℃

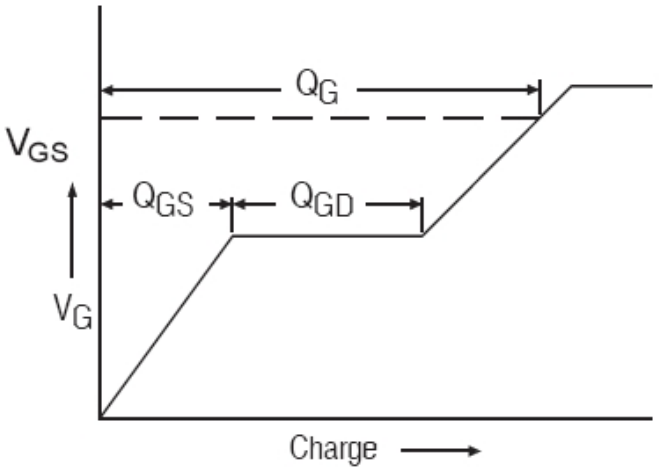
Test Circuit

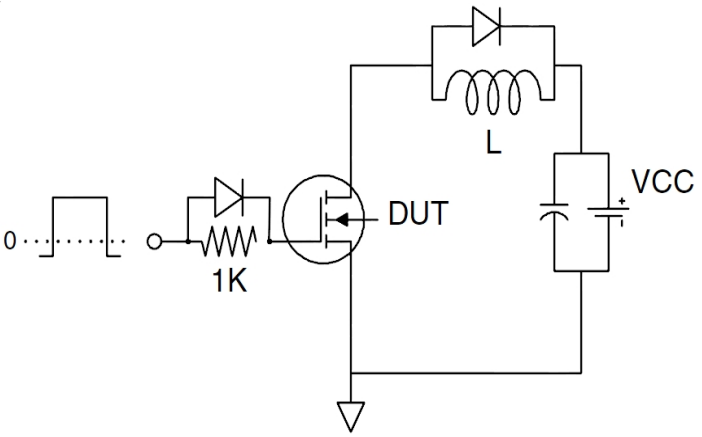
1) E_{AS} Test Circuits



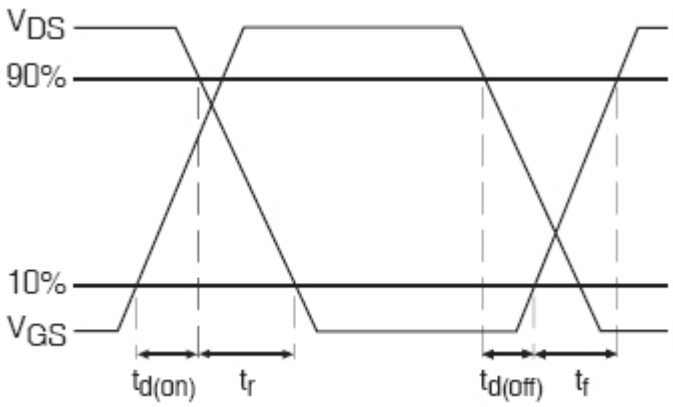


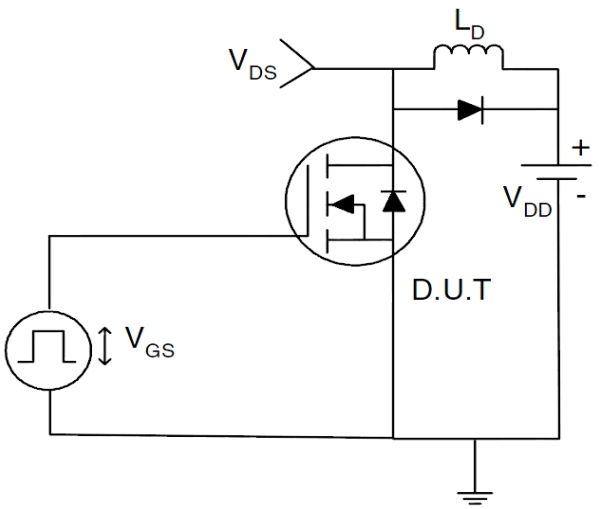
2) **Gate Charge Test Circuit:**





3) **Switch Time Test Circuit:**





TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS (Curves)

Figure1. Output Characteristics

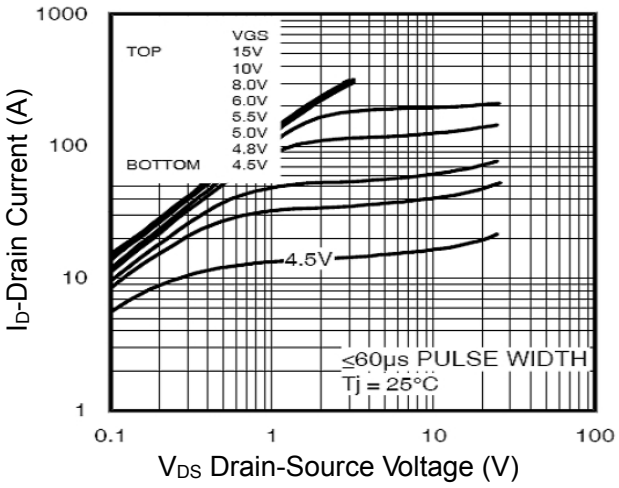


Figure2. Transfer Characteristics

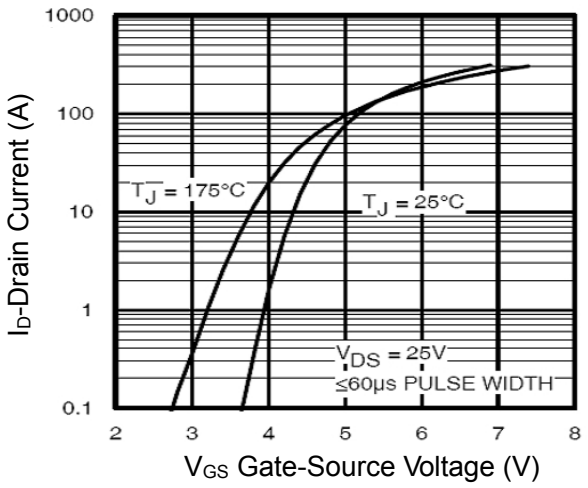


Figure3. Rdson Vs Drain Current

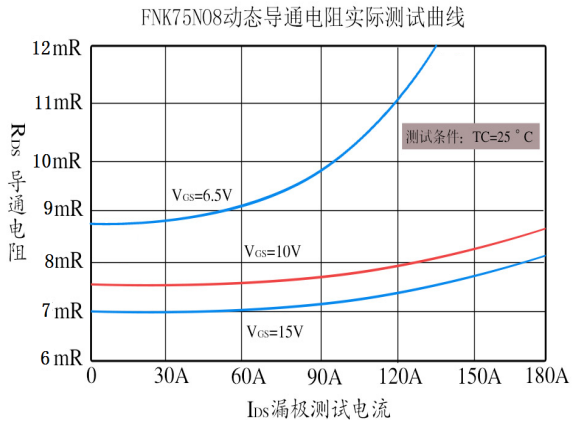


Figure4. Rdson Vs Junction Temperature

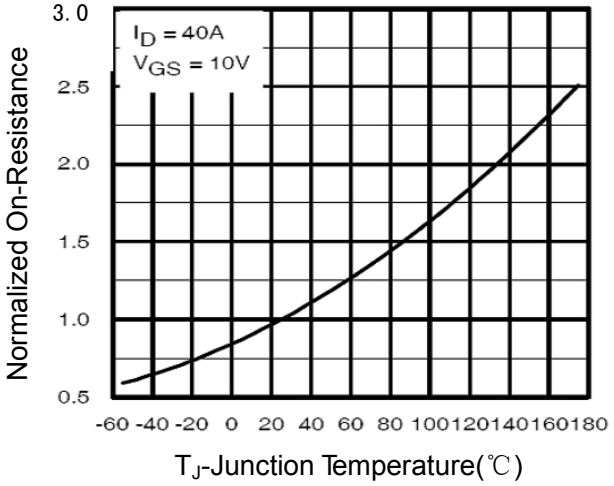


Figure5. Gate Charge

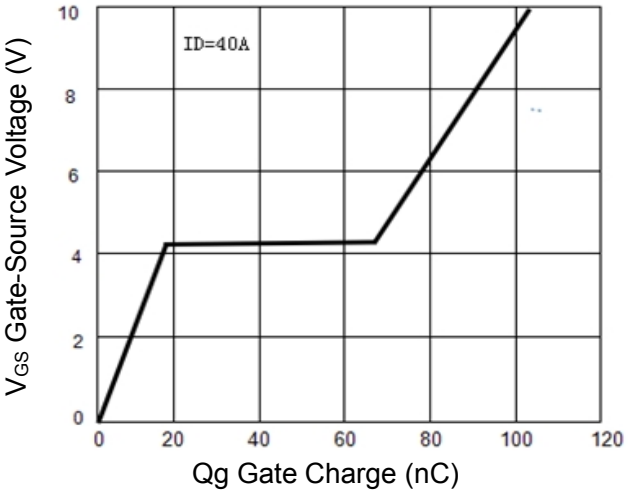


Figure6. Source- Drain Diode Forward

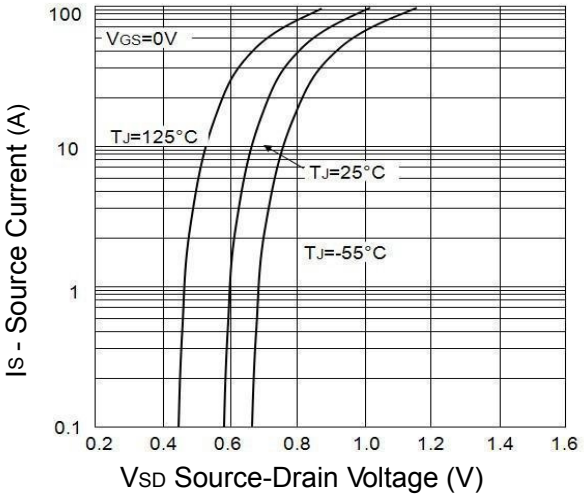


Figure7. Capacitance vs Vds

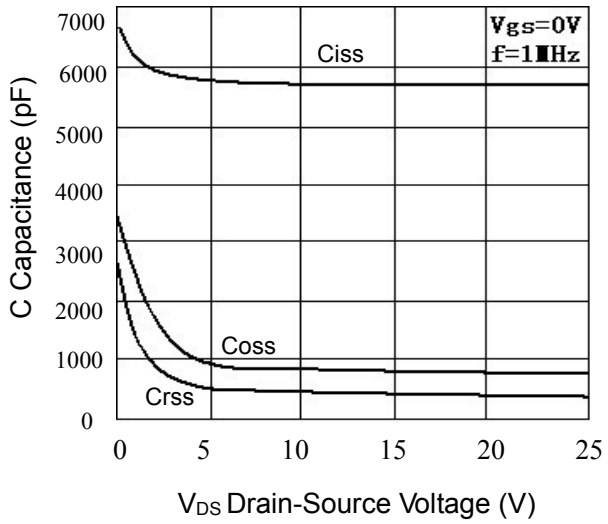


Figure8. Safe Operation Area

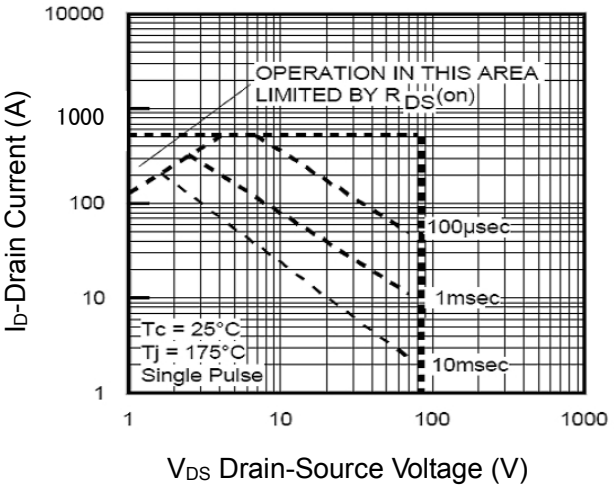


Figure9. BVDSS vs Junction Temperature

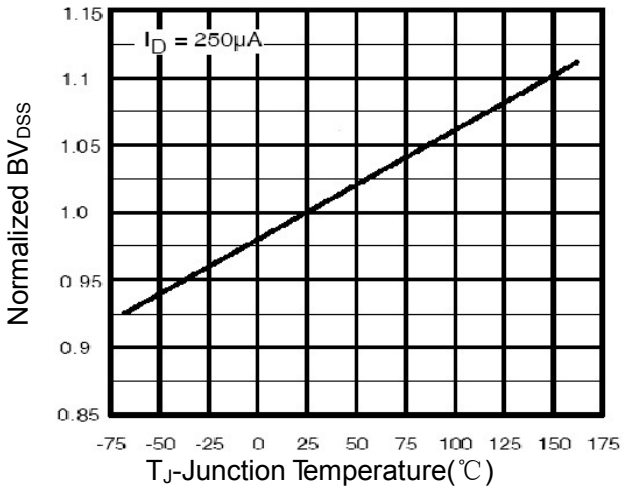


Figure10. VGS(th) vs Junction Temperature

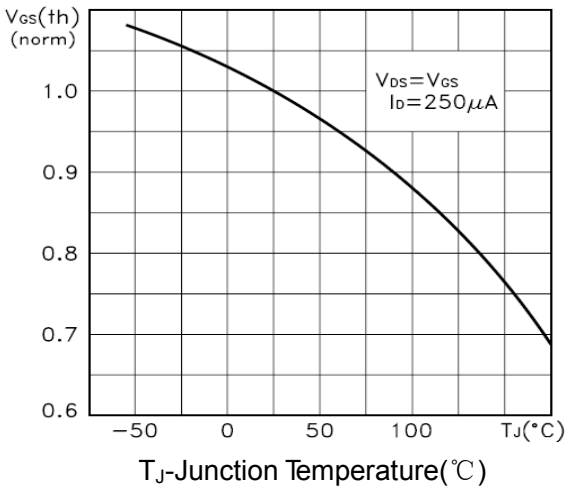
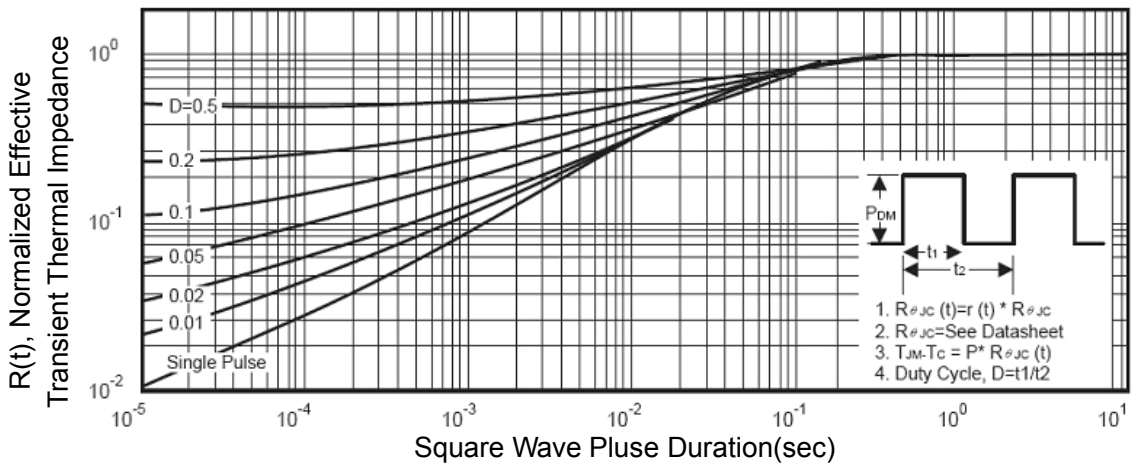
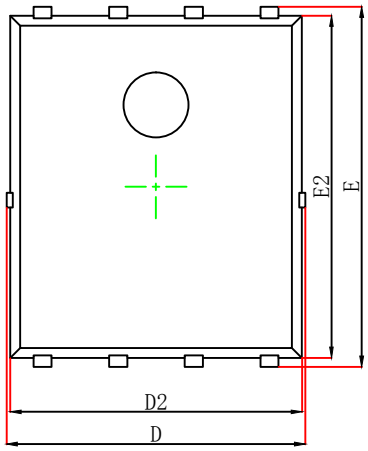


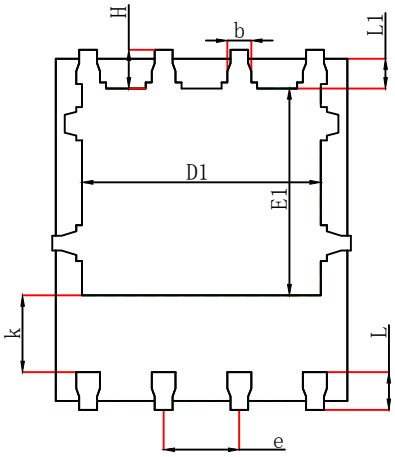
Figure11. Normalized Maximum Transient Thermal Impedance



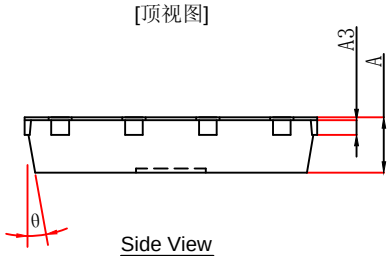
PDFNWB5×6-8L(P1.27T0.95) PACKAGE OUTLINE DIMENSIONS



Top View
[顶视图]



Bottom View
[背视图]



Side View
[侧视图]

Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.000	0.035	0.039
A3	0.254REF.		0.010REF.	
D	4.944	5.096	0.195	0.201
E	5.974	6.126	0.235	0.241
D1	3.910	4.110	0.154	0.162
E1	3.375	3.575	0.133	0.141
D2	4.824	4.976	0.190	0.196
E2	5.674	5.826	0.223	0.229
k	1.190	1.390	0.047	0.055
b	0.350	0.450	0.014	0.018
e	1.270TYP.		0.050TYP.	
L	0.559	0.711	0.022	0.028
L1	0.424	0.576	0.017	0.023
H	0.574	0.726	0.023	0.029
θ	10°	12°	10°	12°

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